

Amended Claims 3, 4, 6-9, 12, 13, and 15-22

3. (Amended) A method for drying substrate as set forth in claim 1, wherein the method determines an introduction direction of the drying fluid into the processing vessel and determines an introduction initial speed of the drying fluid so as to expand the drying fluid up to the entire width of the substrates on the fluid surface of the cleaning fluid.

4. (Amended) A method for drying substrate as set forth in claim 1, wherein the method supplies inert gas into the processing vessel following exhausting of the cleaning fluid from the processing vessel.

6. (Amended) A method for drying substrate as set forth in claim 1, wherein the method changes supporting position of the substrates following exhausting of the cleaning fluid from the processing vessel.

7. (Amended) A method for drying substrate as set forth in claim 4, wherein the method makes the interior of the processing vessel to be inert gas environment prior to exhausting of the cleaning fluid from the processing vessel.

8. (Amended) A method for drying substrate as set forth in claim 1, wherein the method carries out the cleaning process and the following drying processing under a room temperature.

9. (Amended) A method for drying substrate as set forth in claim 1, wherein the method flows the drying fluid by the pressure of inert gas which is supplied to the nozzle.

12. (Amended) A device for drying substrate as set forth in claim 10, wherein the drying fluid supplying means is a means for determining an introduction direction of

BEST AVAILABLE

the drying fluid into the processing vessel and determines an introduction initial speed of the drying fluid so as to expand the drying fluid up to the entire width of the substrates on the fluid surface of the cleaning fluid.

13. (Amended) A device for drying substrate as set forth in claim 10, further comprising insert gas supplying means for supplying inert gas into the processing vessel following exhausting of the cleaning fluid from the processing vessel.

15. (Amended) A device for drying substrate as set forth in claim 10, wherein the supporting means is a means having a cleaning fluid introduction groove which follows in lower ward direction with respect to the substrate supporting section.

16. (Amended) A device for drying substrate as set forth in claim 10, wherein the supporting means is a pair of supporting means for selectively supporting different positions of the substrates which positions are different from one another, and further comprising supporting position control means for changing the supporting position of the substrates by the supporting means following exhausting of the cleaning fluid from the processing vessel.

17. (Amended) A device for drying substrate as set forth in claim 13, further comprising environment determination means for making the interior of the processing vessel to be inert gas environment prior to exhausting of the cleaning fluid from the processing vessel.

18. (Amended) A device for drying substrate as set forth in claim 10, further comprises nozzle position control means for moving the nozzle towards the substrates following exhausting of the cleaning fluid from the processing vessel.

19. (Amended) A device for drying substrate as set forth in claim 10, further comprising circulation means for circulating the drying fluid when ejection is not carried out.

20. (Amended) A device for drying substrate as set forth in claim 10, wherein a number of nozzles is determined in response to the size of the substrate and the pitch of the substrates.

21. (Amended) A device for drying substrate as set forth in claim 10, wherein the nozzle has drying fluid ejection holes a number of which is greater than the number of the substrates by 1 which substrates are dried simultaneously.

22. (Amended) A device for drying substrate as set forth in claim 10, further comprising inert gas supplying means for supplying inert gas to the nozzle so as to flow the drying fluid by the pressure of inert gas.